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(54) **METHOD OF FORMING RESIST PATTERN**

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(58) **Field of Classification Search**

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(57) **ABSTRACT**

A method of forming a resist pattern, including forming a resist film on a substrate using a resist composition comprising a base component that exhibits increased solubility in an alkali developing solution and a photo-base generator component; exposing the resist film; baking the exposed resist film, such that, at an exposed portion thereof, the base generated from the photo-base generator component upon the exposure and an acid provided to the resist film are neutralized, and at an unexposed portion of the resist film, the solubility of the base component in an alkali developing solution is increased by the acid provided to the resist film; and subjecting the resist film to alkali development, thereby forming a negative-tone resist pattern in which the unexposed portion of the resist film has been dissolved and removed.